

M5M44265CJ, TP-5, -6, -7, -5S, -6S, -7S

HYPER PAGE MODE 4194304-BIT (262144-WORD BY 16-BIT) DYNAMIC RAM

DESCRIPTION

This is a family of 262144-word by 16-bit dynamic RAMs with Hyper Page mode function, fabricated with the high performance CMOS process, and is ideal for the buffer memory systems of personal computer graphics and HDD where high speed, low power dissipation, and low costs are essential. The use of double-layer metalization process technology and a single-transistor dynamic storage stacked capacitor cell provide high circuit density at reduced costs. Multiplexed address inputs permit both a reduction in pins and an increase in system densities. Self or extended refresh current is low enough for battery back-up application. This device has $2\overline{CAS}$ and $1\overline{W}$ terminals with a refresh cycle of 512 cycles every 8.2ms.

FEATURES

Type name	RAS access time (max. ns)	CAS access time (max. ns)	Address access time (max. ns)	OE access time (max. ns)	Cycle time (min. ns)	Power dissipation (typ. mW)
M5M44265CXX-5.5S	50	13	25	13	90	625
M5M44265CXX-6.6S	60	15	30	15	110	550
M5M44265CXX-7.7S	70	20	35	20	130	475

XX=J, TP

- Standard 40 pin SOJ, 44 pin TSOP (II)
- Single $5V \pm 10\%$ supply
- Low stand-by power dissipation
 - CMOS Input level ----- 5.5mW(Max)
 - CMOS Input level ----- $550 \mu W$ (Max) *
- Operating power dissipation
 - M5M44265Cxx- 5.5S ----- 688mW (Max)
 - M5M44265Cxx- 6.6S ----- 605mW (Max)
 - M5M44265Cxx- 7.7S ----- 523mW (Max)
- Self refresh capability*
 - Self refresh current ----- $150 \mu A$ (max)
- Extended refresh capability
 - Extended refresh current ----- $150 \mu A$ (max)
- Hyper page mode (512-column random access), Read-modify-write, RAS-only refresh, \overline{CAS} before \overline{RAS} refresh, Hidden refresh capabilities.
- Early-write mode, \overline{OE} and \overline{W} to control output buffer impedance
- 512 refresh cycles every 8.2ms (A0 ~ A8)
- 512 refresh cycles every 128ms (A0 ~ A8)*
- Byte or Word control for Read/Write operation ($2\overline{CAS}$, $1\overline{W}$ type)
 - *:Applicable to self refresh version(M5M44265CJ, TP -5S, -6S, -7S :option) only

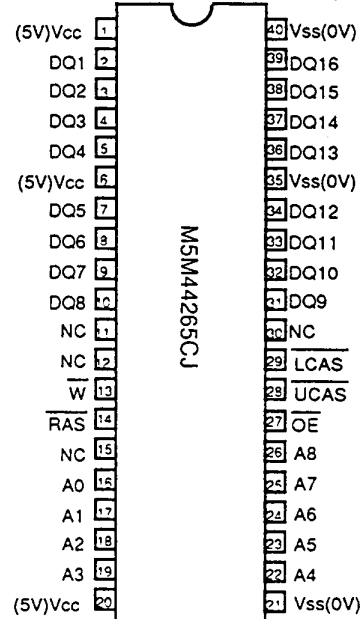
APPLICATION

Microcomputer memory, Refresh memory for CRT,
Frame Buffer memory for CRT

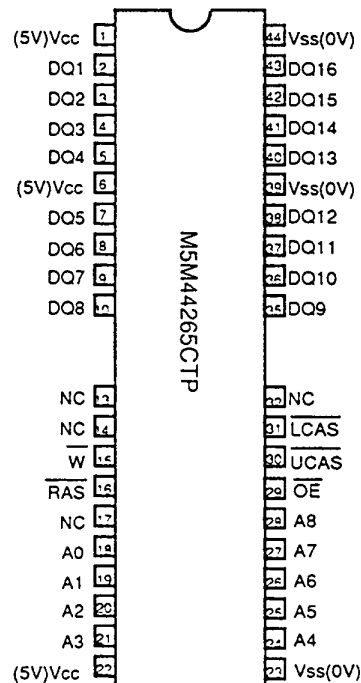
PIN DESCRIPTION

Pin Name	Function
A0-A8	Address Inputs
DQ1-DQ16	Data Inputs / Outputs
\overline{RAS}	Row Address Strobe Input
\overline{LCAS}	Lower Byte Control Column Address Strobe Input
\overline{UCAS}	Upper Byte Control Column Address Strobe Input
\overline{W}	Write Control Input
\overline{OE}	Output Enable Input
Vcc	Power Supply (+5V)
Vss	Ground (0V)

PIN CONFIGURATION (TOP VIEW)



Outline 40POK(400mil SOJ)



Outline 44P3W(400mil TSOP Nomal Bend)

NC: NO CONNECTION

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FUNCTION

In addition to Hyper Page Mode, normal read, write and read-modify-write operations the M5M44265CJ, TP provides a number of other functions, e.g., RAS-only refresh, and

delayed-write. The input conditions for each are shown in Table 1.

Table 1 Input conditions for each mode

Operation	Inputs					Input/Output	
	RAS	LCAS	UCAS	\overline{W}	\overline{OE}	DO1~DO8	DO9~DO16
Lower byte read	ACT	ACT	NAC	NAC	ACT	Dout	OPN
Upper byte read	ACT	NAC	ACT	NAC	ACT	OPN	DOUT
Word read	ACT	ACT	ACT	NAC	ACT	DOUT	DOUT
Lower byte write	ACT	ACT	NAC	ACT	NAC	DIN	DNC
Upper byte write	ACT	NAC	ACT	ACT	NAC	DNC	DIN
Word write	ACT	ACT	ACT	ACT	NAC	DIN	DIN
RAS only refresh	ACT	NAC	NAC	DNC	DNC	OPN	OPN
Hidden refresh	ACT	ACT	ACT	NAC	ACT	DOUT	DOUT
CAS before RAS (Extended*) refresh	ACT	ACT	ACT	DNC	DNC	OPN	OPN
Self refresh*	ACT	ACT	ACT	DNC	DNC	OPN	OPN
Stand-by	NAC	DNC	DNC	DNC	DNC	OPN	OPN

Note : ACT : active, NAC : nonactive, DNC : don't care, OPN : open

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